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## FAIRCHILD

SEMICONDUCTOR®

## KSC2785

## Audio Frequency Amplifier & High Frequency OSC.

- Complement to KSA1175
- Collector-Base Voltage : V<sub>CBO</sub>=60V



1.Emitter 2. Collector 3. Base

## NPN Epitaxial Silicon Transistor

Absolute Maximum Ratings Ta=25°C unless otherwise noted

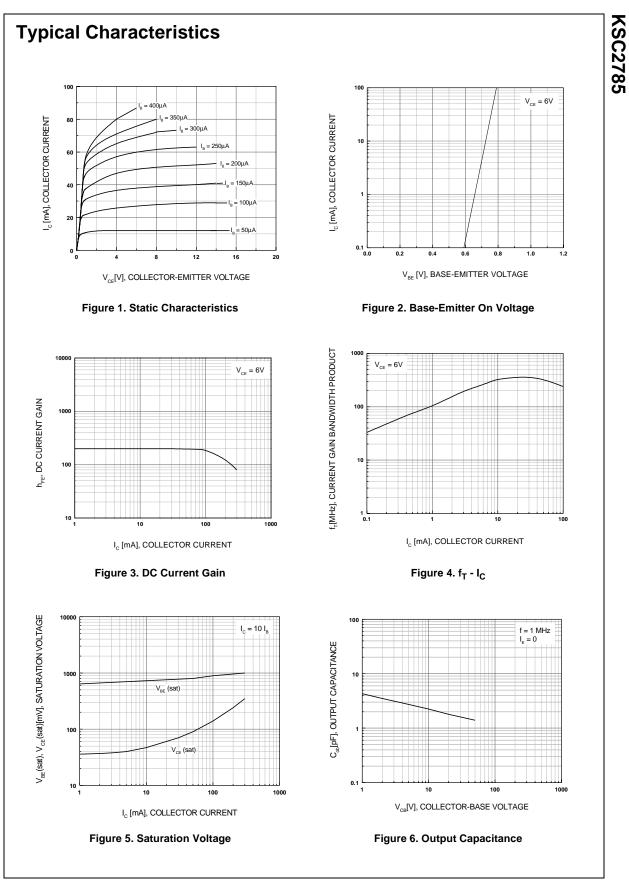
Symbol	Parameter	Value	Units	
V <sub>CBO</sub>	Collector-Base Voltage	60	V	
	Collector-Emitter Voltage	50	V	
V <sub>CEO</sub> V <sub>EBO</sub>	Emitter-Base Voltage	5	V	
I <sub>C</sub>	Collector Current	150	mA	
P <sub>C</sub>	Collector Power Dissipation	250	mW	
TJ	Junction Temperature	150	°C	
T <sub>STG</sub>	Storage Temperature	-55 ~ 150	°C	

### **Electrical Characteristics** $T_a=25^{\circ}C$ unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Тур.	Max.	Units
BV <sub>CBO</sub>	Collector-Base Breakdown Voltage	I <sub>C</sub> =100μA, I <sub>E</sub> =0	60			V
BV <sub>CEO</sub>	Collector-Emitter Breakdown Voltage	I <sub>C</sub> =10mA, I <sub>B</sub> =0	50			V
BV <sub>EBO</sub>	Emitter-Base Breakdown Voltage	I <sub>E</sub> =10μA, I <sub>C</sub> =0	5			V
I <sub>CBO</sub>	Collector Cut-off Current	V <sub>CB</sub> =40V, I <sub>E</sub> =0			0.1	μΑ
I <sub>EBO</sub>	Emitter Cut-off Current	V <sub>EB</sub> =3V, I <sub>C</sub> =0			0.1	μΑ
h <sub>FE</sub>	DC Current Gain	V <sub>CE</sub> =6V, I <sub>C</sub> =1.0mA	70		700	
V <sub>CE</sub> (sat)	Collector-Emitter Saturation Voltage	I <sub>C</sub> =100mA, I <sub>B</sub> =10mA		0.15	0.3	V
f <sub>T</sub>	Current Gain Bandwidth Product	V <sub>CE</sub> =6V, I <sub>C</sub> =10mA		300		MHz
C <sub>ob</sub>	Output Capacitance	V <sub>CB</sub> =6V, I <sub>E</sub> =0, f=1MHz		2.5		pF
NF	Noise Figure	$V_{CE}$ =6, I <sub>C</sub> =0.5mA f=1KHz, R <sub>S</sub> =500 $\Omega$		4.0		dB

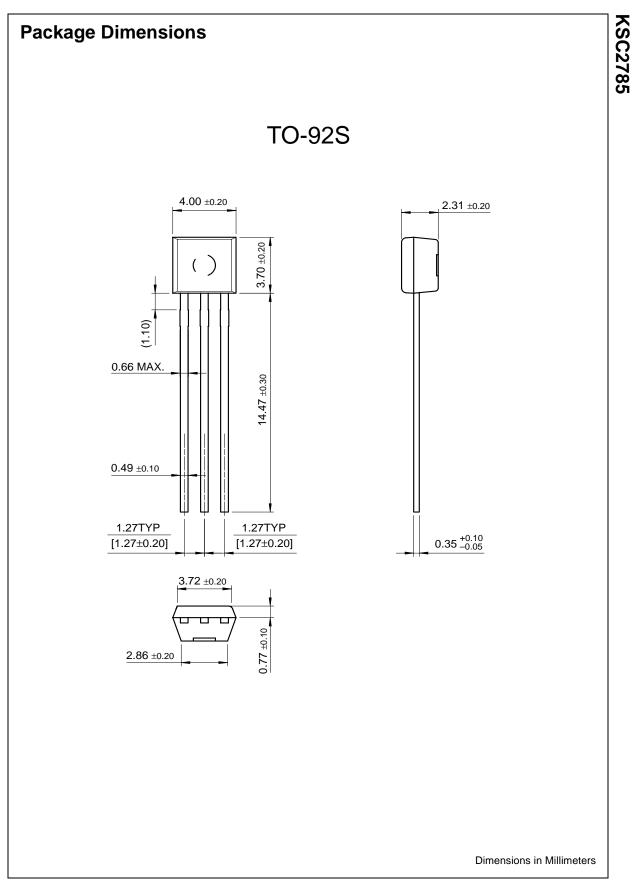
## h<sub>FE</sub> Classification

Classification	0	Y	G	L		
h <sub>FE</sub>	70 ~ 140	120 ~ 240	200 ~ 400	350 ~ 700		



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